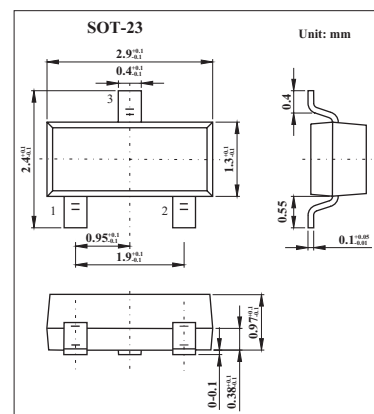


## Silicon Epitaxial Schottky Barrier Diode

## 1SS351

## ■ Features

- Series connection of 2 elements in a small-sized package facilitates high-density mounting and permits 1SS351-applied equipment to be made smaller.
- Small interterminal capacitance ( $C=0.69\text{pF}$  typ).
- Small forward voltage ( $V_F=0.23\text{V}$  max).

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

| Parameter            | Symbol    | Value       | Unit             |
|----------------------|-----------|-------------|------------------|
| Reverse Voltage      | $V_R$     | 5           | V                |
| Forward Current      | $I_F$     | 30          | mA               |
| Junction Temperature | $T_j$     | 125         | $^\circ\text{C}$ |
| Storage temperature  | $T_{stg}$ | -55 to +125 | $^\circ\text{C}$ |

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

| Parameter                 | Symbol | Conditions                             | Min | Typ  | Max  | Unit          |
|---------------------------|--------|----------------------------------------|-----|------|------|---------------|
| Forward Voltage           | $V_F$  | $I_F = 1\text{ mA}$                    |     |      | 0.23 | V             |
| Forward Current           | $I_F$  | $V_F = 0.5\text{ V}$                   | 30  |      |      | mA            |
| Reverse Current           | $I_R$  | $V_R = 0.5\text{ V}$                   |     |      | 25   | $\mu\text{A}$ |
| Interterminal Capacitance | $C$    | $V_R = 0.2\text{ V}, f = 1\text{ MHz}$ |     | 0.69 | 0.9  | pF            |

## ■ Marking

|         |    |
|---------|----|
| Marking | CH |
|---------|----|